MCH3481

Power MOSFET 20V, 104mΩ, 2A, Single N-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- Low On-Resistance
- 1.2V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

Load Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	20	V
Gate to Source Voltage	VGSS	±9	V
Drain Current (DC)	ID	2	А
Drain Current (Pulse) PW \leq 10 μ s, duty cycle \leq 1%	IDP	8	A
Power Dissipation When mounted on ceramic substrate (900mm ² \times 0.8mm)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² \times 0.8mm)	R _{θJA}	156.2	°C/W

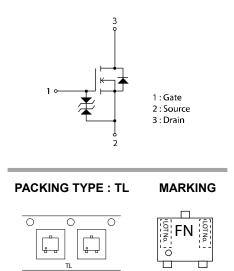


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VDSS	R _{DS} (on) Max	ID Max
20V	104mΩ@ 4.5V	
	147mΩ@ 2.5V	24
	20V 203mΩ@ 1.8V	
	540mΩ@ 1.2V	

ELECTRICAL CONNECTION N-Channel



ORDERING INFORMATION See detailed ordering and shipping information on page 5 of this data sheet.

Unit

V

μΑ

μA

٧ S

mΩ

mΩ

mΩ

mΩ pF рF pF ns ns ns ns nC nC

nC

V

1.2

0.53

0.85

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Parameter	Symbol Conditions		min	typ	max
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20		
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1
Gate to Source Leakage Current	IGSS	V _{GS} =±7.2V, V _{DS} =0V			±10
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	0.3		0.9
Forward Transconductance	9FS	V _{DS} =10V, I _D =1A		2.4	
Static Drain to Source On-State Resistance	R _{DS} (on)1	ID=1A, VGS=4.5V		80	104
	R _{DS} (on)2	ID=0.5A, VGS=2.5V		105	147
	R _{DS} (on)3	ID=0.3A, VGS=1.8V		135	203
	R _{DS} (on)4	ID=0.1A, VGS=1.2V		270	540
Input Capacitance	Ciss			175	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		30	
Reverse Transfer Capacitance	Crss			25	
Turn-ON Delay Time	t _d (on)			6.6	
Rise Time	tr			27	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		28	
Fall Time	tf			19	
Total Gate Charge	Qg			2.9	
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		0.46	

IS=2A, VGS=0V Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

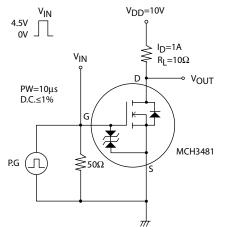
Qgd

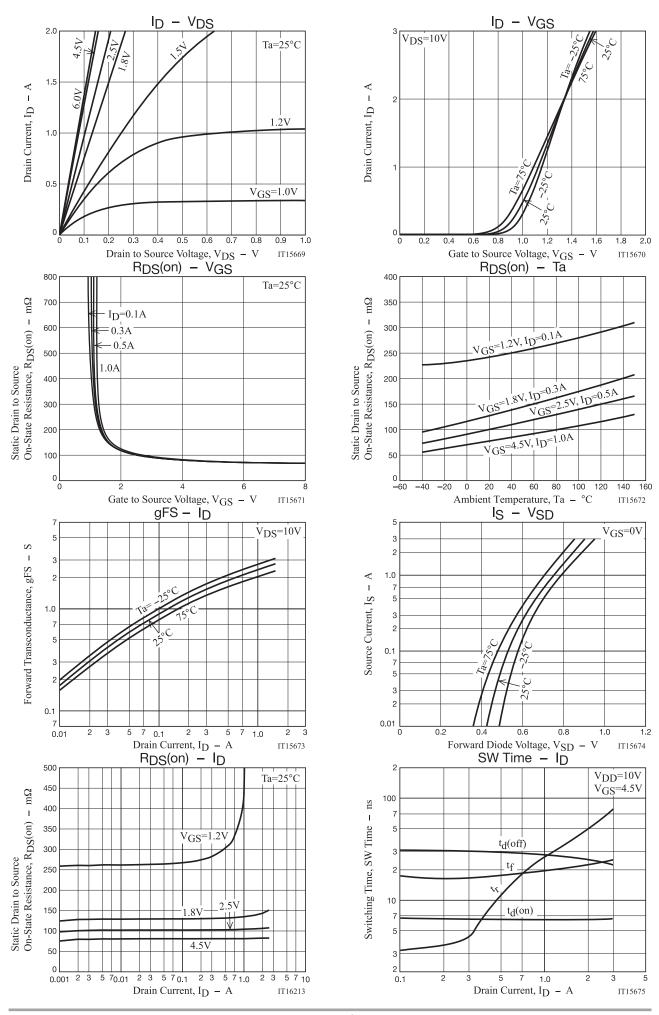
VSD

Switching Time Test Circuit

Gate to Drain "Miller" Charge

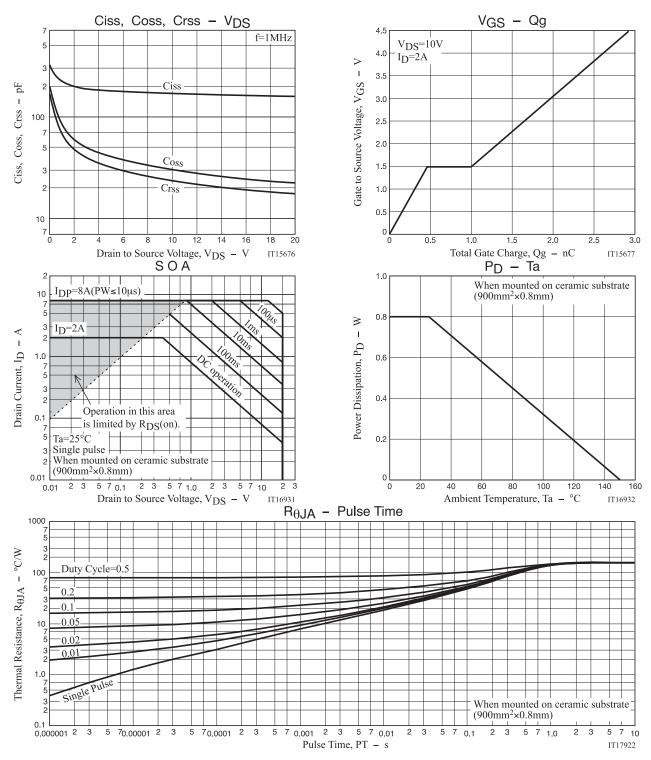
Forward Diode Voltage





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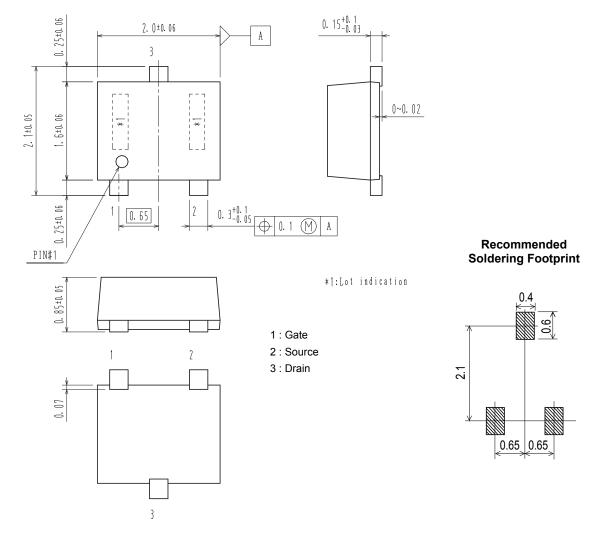
MCH3481



PACKAGE DIMENSIONS

unit : mm

SC-70FL / MCPH3 CASE 419AQ ISSUE O



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
MCH3481-TL-H	EN	SC-70FL / MCPH3		
MCH3481-TL-W	W FN (Pb-Free / Halogen Free)		3,000 / Tape & Reel	

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the MCH3481 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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